Multi Standard Feature Phone Integrated Circuit

Description

The U3810BM multi-standard feature phone circuit is designed to be used with a microcontroller using a 2-wire serial bus. It performs all speech and line interface functions required in an electronic telephone set: the ringing function with switching regulator and melody generator, the DTMF dialling, the loudhearing with antilarsen and antidistortion systems, a power supply, a clock and a reset for the microcontroller. Transmit, receive and loudhearing gains control / AGC range / DTMF frequencies, pre-emphasis and level / melody generator, and mutes are programmable through the serial bus.

Block diagramm

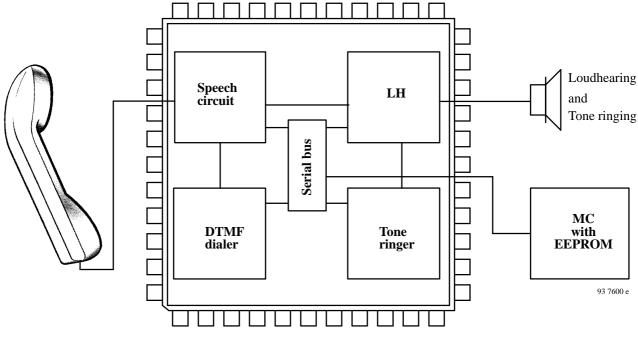


Figure 1

Applications

- Feature phones
- Answering machines
- Fax machines

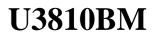
Benefits

- Complete system integration of analog signal processing and digital control circuitry
- One IC for various PTT standards, e.g. programmable specification via μC
- Only three low-cost transducers needed (instead of four)

Features

- Slope of DC characteristics adjustable by an external resistor
- Gain of transmit and receive amplifiers automatically adjusted by line length control
- Regulation range adjustable by the serial bus
- Possibility of fixed gain (PABX)
- Sidetone balancing system adjustable with line length or by the serial bus
- Dynamic impedance adjustable by external components
- Stabilized power supply for peripherals
- Confidence level during dialling
- +6 dB possibility on second stage transmit gain
- Transmit and receive gains adjustable by serial bus
- Extra transmit input for handsfree and answering machine purpose
- +6 dB possibility on receive gain
- Receive amplifier for dynamic or piezo-electric earpieces
- Extra receive output for handsfree purpose
- High impedance microphone inputs suitable for dynamic, magnetic, piezo-electric or electret microphone
- Distortion of line signal and sidetone prevented by dynamic range limitation in transmission (anti-clipping)
- Squelch system in transmission prevents "room noise" are being transmitted, and improves anti-larsen efficiency (can be inhibited).

- Loudhearing gain programmable in eight steps of 4 dB, using the serial bus, or linearly adjusted, using a potentiometer
- Anti-larsen system efficiency is increased when inhibiting squelch
- Loudhearing anti-distortion system by automatic gain control versus available current and voltage
- Switching regulator in ringing phase
- Input ringing detection, threshold and impedance adjustable with external resistors
- Ringing zero crossing information for external microprocessor
- Ringing programmable gain in eight steps of 4 dB using the serial bus
- Melody generator, with 30 frequencies in steps of semi tones, driven by serial bus
- Internal speed-up circuit permits a faster charge of VDD and VCC capacitor
- DTMF dialer driven by serial bus, in particular level and pre-emphasis adjustment
- Ability to transmit a confidence tone in speech mode using melody generator frequencies
- Five independent mutes driven by serial bus (two in transmission, two in reception, one for the transmit / receive loop)
- Standard low-cost ceramic 455 kHz / clock output for the microcontroller
- Extra loudhearing input for answering machines, handsfree and base station of phones cordless with loudhearing



Block diagram

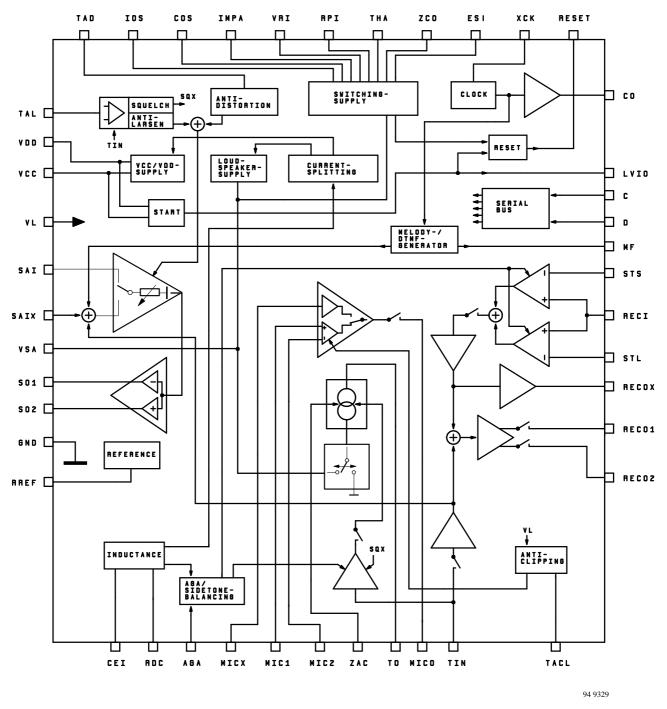


Figure 2

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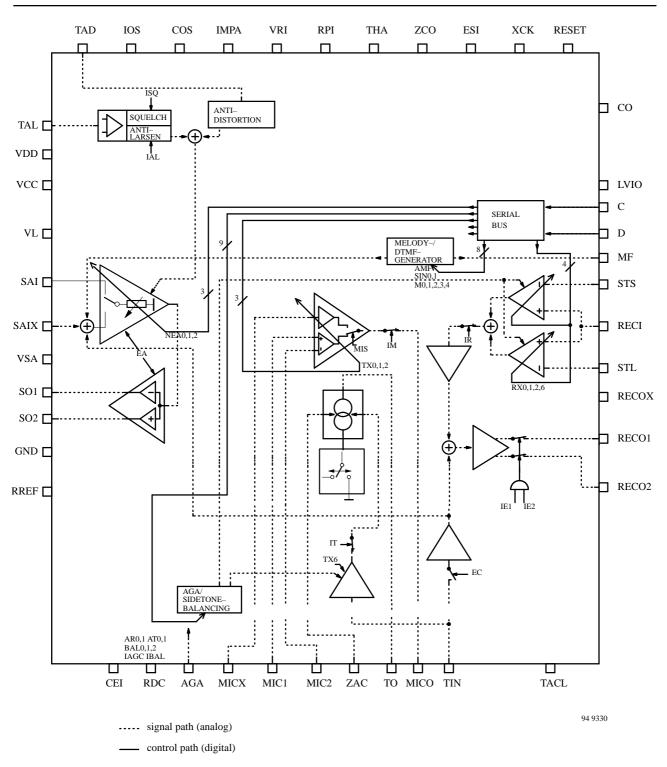


Figure 3 Digital adjustment of the analog parameters by the serial bus microprocessor-interface

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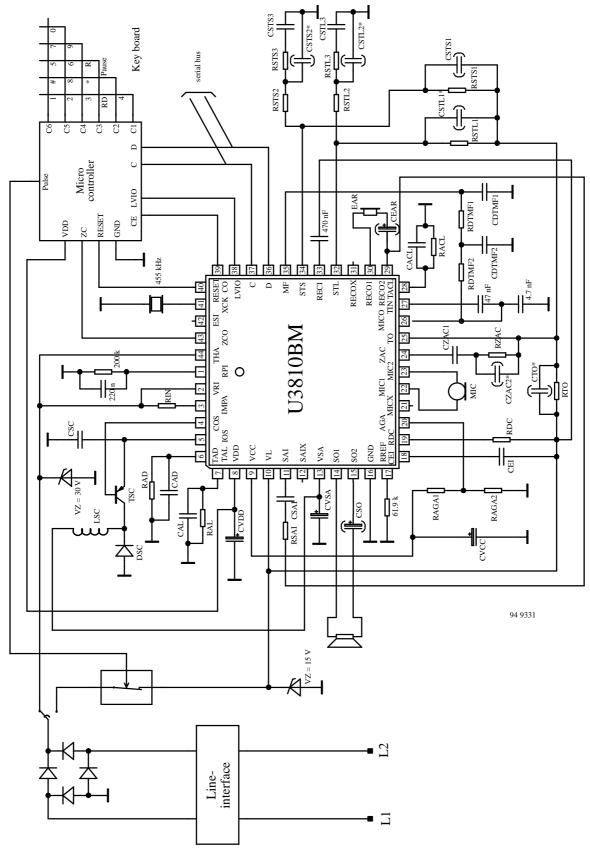


Figure 4 Application for feature phone

Typical value of external components

Components	Min.	Тур.	Max.
RIN	$0.3 \text{ M}\Omega$	1.0 MΩ	1.5 MΩ
CSC		0.1 μF	
TSC		2N5401A	
LSC		1 mH	
DSC		SD103A	
RAD		100 kΩ	
CAD		470 nF	
CAL		470 nF	
RAL		$68 \text{ k}\Omega$	82 kΩ
CVDD		470 µF	
RSAI		20 kΩ	
CSAI		0.1 μF	
CVSA		220 µF	
CSO		47 μF	
CVCC		100 µF	
RAGA1		100 kΩ	
RAGA2		51 kΩ	
CEI		0.47 μF	
RDC		20 kΩ	
RTO		62 Ω	
(CTO		0.33 µF)	
CZAC1		0.47 μF	
RZAC		12 kΩ	

Components	Min.	Тур.	Max.
(CZAC2		470 pF)	
RDTMF1		240 kΩ	
RDMTF2		$330 \text{ k}\Omega$	
CDTMF1		4.7 nF	
CDTMF2		220 pF	
CACL		0.47 μF	
RACL		$6.8 \mathrm{M}\Omega$	
CEAR		4.7 μF	
Earphone		$\sim 1 \ \mathrm{k}\Omega$	
Loudspeaker		$\sim 100 \ \Omega$	
RSTL1		6.2 kΩ	
(CSTL1		330 pF)	
RSTS1		6.2 kΩ	
(CSTS1		330 pF)	
RSTL2		43 kΩ	
RSTS2		18 kΩ	
RSTL3		100 kΩ	
RSTS3		$75 \ \mathrm{k}\Omega$	
CSTL3		10 nF	
CSTS3		10 nF	
CSTS2		470 pF	
CSTL2		1.2 nF	
X1		CSB455E (Murata)	

Pin description

Pin	Symbol	Function
1	RPI	Ringing power information. The RC combination smooths the drive current of the loudspeaker amplifier.
2	VRI	Tone-ringer supply voltage. The rectified ringing voltage is delivered to VRI and then converted into the lower supply voltage, VSA, by the converter.
3	IMPA	External adjustment of input ringing impedance. IMPA is adjusted with a resistance between pin 2 and 3. $ZIN = RIN/100$
4	COS	Control output switching supply. COS drives the base of the external switching transis- tor of the converter.
5	IOS	Current output of switching supply. This output provides a constant current, which supplies the external part of converter. The magnitude of the current depends on the VRI voltage and the value of resistance RIN.
6	TAD	Adjustment of antidistortion time constant in loudhearing with external RC combination.
7	TAL	Adjustment of antilarsen time constant in loudhearing with external RC combination.
8	VDD	External logic supply.
9	VCC	Power supply for peripherals. VCC and VDD are stabilized supply voltages buffered with external capacitors. They are derived internally from the same voltage source, but are separated from each other by electronic switches. VDD also supplies the digital part of the circuit and is achieved in all three modes: speech mode, ringing mode and operation with external supply. According to the application, peripherial modules are connected to VDD which, in addition to speech mode, must be supplied at least in one of the two other modes. The digital part of circuit and microprocessor must continue operating during line breaks, as they occur during pulse dialing or during flash-signal transmission. Since VDD in this time intervals is fed only from the buffer capacity, the power consumption from VDD must not cause the total voltage dump. VCC supplies no internal parts of circuit and is supplied exclusively in speech mode. External components, which must operate only in this mode, can be connected here. The power is drawn only from the relevant buffer capacitor in the supply intervals during pulse dialing or flash-signal transmission.
10	VL	Line voltage.
11	SAI	Speaker amplifier input. The signal coming from the receive part, e.g. from REC01 or REC02, is fed in here.
12	SAIX	Speaker amplifier input for special application i.e. answering machine. SAIX is selected via the serial bus. SAIX has to be selected for ringing. IF ringing, Antidistortion and Antilarsen are disabled.
13	VSA	Supply voltage for the loudhearing amplifier. Stabilized supply voltage buffered with an external capacitor for the loudhearing amplifier and zero crossing detector; aditional connection point for an external supply. In speech mode, VSA is supplied by the analog part of the circuit. In this case, the stabilization point is adjusted to the DC line voltage VSA= VL/1.5. In ringing mode, and VSA is supplied directly from the con- verter. The stabilization point is permanently set. The logic supply, VDD, is fed by a switch from VSA. VSA=5.2V. In the case of an external supply, VSA serves as a point for a current from a power supply. The stabilization point of VSA and supply for the logic correspond to the operation conditions in ringing mode.
14	SO1	Loudspeaker output 1.
15	SO2	Loudspeaker output 2. Differential output of loudhearing amplifier. The loudspeaker can also be connected asymmetrically to ground or to VSA via a capacitor at one of the two outputs. As a result of this connection there is a bigger output power in reference to low line currents and loudspeakers with low impedance, while the differential connection method results in a higher power output and lower harmonic distortion with medium or high line currents and/or loudspeaker impedances

Pin description

Pin	Symbol	Function
16	GND	Ground.
17	RREF	External reference resistor. Connection for external reference resistor to generate the reference current. All basic currents of the circuit which must satisfy certain absolute accuracy requirements depend on this current.
18	CEI	Capacitor for electronic inductance. Connection for capacitor of the electronic coil. The circuit contains a first order RC-active low-pass filter. The capacitor is connected externally between CEI and VL.
19	RDC	DC characteristic slope adjustment. A voltage across resistor RDC is proportional to the dc line voltage. This means the current flow through RDC is also proportional to the line voltage. This current drives the supply currents drawn from VL by the most important loads, and therefore defines the total current consumption of the circuit. Adjustment to the slope characteristic is realized by modification of RDC resistance.
20	AGA	Line length adjustment. Reference voltage level for AGA. The potential at this point defines the start threshold for the AGA and the automatic balancing in the receive part (both can be switched off by the serial bus). The potential is normally formed between VCC and ground using a voltage divider. When the line voltage exceeds the threshold level, the AGA or balancing becomes effective.
21	MICX	Asymmetrical microphone input for special applications. The input of the first stage of the transmit amplifier, selected by the serial bus. Anticlipping is not effective at this input.
22	MIC1	Inverting input of microphone amplifier.
23	MIC2	Noninverting input of microphone amplifier.
24	ZAC	AC impedance adjustment. Adjustment of the ac circuit impedance to the line by changing of RZAC.
25	ТО	Transmit amplifier output. Transmit amplifier output modulates the current flowing into this output (typically 4.8 mA).
26	MICO	Microphone amplifier output. Output MICO; open-circuit potential = 2*Vbe
27	TIN	Transmit and DTMF input. Input of the second transmit stage.
28	TACL	Adjustment of anticlipping time constant with external RC combination. Anticlipping controls the transmitter input level to prevent clipping with high signal levels. The dynamic range of the transmit peak limiter is controlled by an internal circuit.
29	RECO2	Symmetrical output of receive amplifier.
30	RECO1	Symmetrical output of receive amplifier.
31	RECOX	Receive amplifier output for handsfree and answering machine applications.
32	STL	Long line sidetone network.
33	RECI	Receive amplifier input. It is driven by a signal from VL.
34	STS	Short line sidetone network.
35	MF	Multifrequency output. Output DTMF signal and confidence tone in pulse–density modulated form. DTMF signal and confidence tone are generated by special generators in the digital part of the circuit. The DTMF signal consists of two weighted and superimposed pulse-density modulated signals, while in the case of confidence tone, a pulse–density modulated signal is superimposed on a high frequency rectangular–pulse signal with pulse duty factor 0.5. The superimposed signals are sent out to MF for further processing.
36	D	Data input of serial bus (see Pin 37). Serial data input from microprocessor for programming the circuit.

Pin description

Pin	Symbol	Function
37	C	Clock line: 2-wire serial bus. This pin is used together with the data input (pin 36) to transfer data from the microprocessor to the circuit. The last 8 bits, consisting of 5 data bits and 3 address bits, are accepted by the circuit if, during the high phase at pin 37, a positive edge on pin 36 takes place.
38	LVIO	Line voltage information output. State indicator of the line voltage, VL, and the supply voltage, VDD. Indicates to microprocessor whether line voltage VL is present across the circuit and the supply voltage VDD is sufficiently high. If both conditions are fulfilled, LVIO is on high level.
39	СО	Clock output. Output 455 kHz clock pulse for the microprocessor. The 455 kHz clock signal generated in the circuit is amplified and sent to CO. This signal is delivered to the microprocessor as a clock signal. Various internal signals can be output to CO in test mode.
40	RESET	Reset signal for periphery. A reset signal (active low) is generated to clear all registers of the circuit. This can be tapped by peripheral modules, particularly by the microprocessor. This pin enables synchronous resetting of the circuit and peripheral modules.
41	XCK	Clock signal generator. Connector for ceramic resonator (455 kHz). The clock for the digital part of the circuit is generated by a one-pin oscillator, the frequency of which is determined by the ceramic resonator.
42	ESI	Input for external supply information. Input to indicate the operating state external supply. In the case of VSA supplied by a power supply unit, the supply source is connected directly to ESI. ESI is connected to VSA by an external diode in forward mode. The ESI voltage will be one forward voltage higher than the voltage on VSA. This voltage causes the circuit to be in external supply mode.
43	ZCO	Zero crossing output in ringing phase. ZCO operates when the ringer voltage, VRI, and the supply voltage, VSA, are sufficiently high. The output voltage ZCO changes state each time the rectified AC signal of THA crosses the ringing detect turn–on and turn–off thresholds, thus providing information on the frequency of the ring signal. Further analysis of the ring frequency is be done by the microprocessor. Secondly, this pin is used as an input for switching on the test mode. Therefore, a negative voltage of approximately 1 V must be applied to pin 43.
44	THA	Ringing detection threshold adjustment. Input amplitude and frequency identification. The rectified ringing voltage is present at this pin. The circuit evaluates the amplitude of the rectified voltage at THA and the supply voltage VSA (pin 13). If both voltages exceed certain thresholds, the signal present at THA is converted to a rectangular–pulse signal and is sent via pin 43 to the microprocessor. If the frequency is in the required range, the microprocessor initiates transmission of the ringing signal. The start threshold can be raised with a resistor connected in series to pin 44.

Absolute maximum ratings

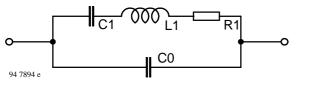
Parameters	Symbol	Value	Unit
DC calling voltage (pin 2)	VRI	35	V
DC calling current (pin 2)	IR	30	mA
Conversation line voltage (pin 10)	VL	15 17	V V pulse 20 ms
Conversation line current	IL	150	mA
Total power dissipation *)	P _{tot}	1	W
Operating temperature range	T _{amb}	-25 to +55	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Junction temperature	Tj	125	°C

Thermal resistance

Parameters	Symbol	Value	Unit
Junction ambient *)	R _{thJA}	70	K/W

Electrical characteristics

 $I_L = 28 \text{ mA}$, $T_{amb} = 25^{\circ}\text{C}$, f = 1 kHz, $R_{DC} = 20 \text{ k}\Omega$, all internal registers cleared, unless otherwise specified



- 455 kHz ceramic resonator: MURATA or equivalent
- Refer to the tests circuits

Figure 5

Resonance factor Q_m = 3100, L1 = 6.1 mH, C1 = 21 pF, CO = 268.5 pF, R1 = 5.5 Ω (Schematic above)

All resistances are specified at 1%, all capacitances at 2%.

Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Line voltage	$I_L = 15 \text{ mA}$	4.2	4.75	5.2		
	$I_L = 28 \text{ mA}$	6.7	7.2	7.5	V	6
	$I_L = 60 \text{ mA}$	12.8	13.45	14.1		
VDD, VCC stabilized	$I_L = 8 \text{ mA}, -\text{Idd}(\text{ICC}) = 0.6$	mA 2.5	2.65			
power supply	$I_L = 28 \text{ mA}, -\text{Idd} (\text{ICC}) = 2.3 \text{ cm}$	mA 3.2	3.45	3.6	V	6
IDD at VDD = 3.5 V	S4 on 3		180	210	μΑ	9
Internal operating supply						
current						
Leakage current				100	nA	
Speed up off threshold	See fig. 11 $I_{Lmax} = 80 \text{ n}$	nA 2.45	2.65	2.8	V	7
VSOFF	$V_L = 4 V$					
Speed up on line-current	See fig. 14 I _L decreasing	g 5.0	5.9	7.5	mA	
ISON	VDD = 2.8 V	V				
Speed up current	$V_L = 4 V$	40	70		mA	7

*) Note: Assembly on PC board $\geq 24 \text{ cm}^2$ assumed

Теміс

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Parameters	Test	condition	ıs		Min.	Тур.	Max.	Unit	Fig.
Transmission									
Transmit gain (note 1)	$V_{\rm MIC} = 3 \rm mV_{rms}$								
	MIS	TX2	TX1	TX0					
on MIC1 / MIC2	max. gain 0	1	1	1	47.0	48.0	49.0	dB	
	min. gain 0	0	0	0	39.8	41.0	42.2	dB	6
									0
	$V_{\text{MICX}} = 5 \text{ mV}_{\text{rms}}$	-		-					
on MICX	MIS		TX1	TX0	43.0	44.0	45.0	dB	
	max.gain 1 min. gain 1	1 0	1 0	$1 \\ 0$	35.8	37.0	38.2	dB	
Gain adjustment of micro-	Gain change betwe		-	-					
phone amplifier	MIC1/MIC2 and c			II OII	0.8	1.0	1.2	dB	6
Transmit gain without AGC	$V_{\text{MIC}} = 3 \text{ mV}_{\text{rms}},$				0.0	110			0
G _T at 28 mA	, where the main states,	TX2	TX1	TX0					
ΔG_T at I _L = 20 to 28 mA		0	1	1	42.6	44.0	45.5		
ΔG_{T} at $I_{L} = 28$ to 60 mA		0	1	1	-0.5	0.0	0.5	dB	6
		0	1	1	-0.5	0.0	0.5		
Gain change between	$V_{MIC} = 3mV_{rms}$:		AT1	AT0					
28 and 60 mA	(MIS = 0)		0	0	3.6	4.1	4.6		
on MIC1 / MIC2			0	1	4.9	5.35	5.9	дĻ	C
on MICX	or $V_{MICX} = 5 \text{ mV}_r$ (MIS = 1)	ms	1 1	0 1	6.3 7.7	6.9 8.2	7.4 8.7	dB	6
L (dD dalta turn angit gain	, ,) A	1	1	1.1	0.2	0.7		
+6 dB delta transmit gain	$I_L = 28 \text{ mA and } 60$ $V_{\text{MIC}} = 1.5 \text{ mV}_{\text{rms}}$		6 – 1		5.4	6.0	6.6	dB	6
Noise at line	GT = max. gain	, DR IA	0 = 1		5.4	0.0	0.0	uD	0
psophometrically weighted	$V_{\text{MIC}} = 0$ (MIS =	0) ISO =	= 0			-79	-75		6
propriorite and weighted	$V_{\text{MIC}} = 0$ (MIS =					-73	-70	dBmp	Ũ
	$V_{\text{MICX}} = 0$ (MIS =						-64	1	
*Max. gain is without +6 dB	function which is e	specially	devoted	for DTI	MF	1	1		
Muted gain	$V_{\rm MIC} = 3 \rm mV_{\rm rms}$ (· ·							
	$V_{\text{MIC}} = 5 \text{ mV}_{\text{rms}}$ (
	(at max. and min.								
on MIC1 / MIC2			Bit IM =		65			dB	6
MCV			Bit IT =	1	65			dB	
on MICX	$V_{\text{MIC}} = 3 \text{ mV}_{\text{rms}}$ (60 60			dB dB	
Microphone input	$V_{\rm MIC} = 5 \ \rm mV_{rms}$ (viis – 0)							
impedance									
on MIC1/MIC 2	$V_{\rm MIC} = 3 \rm mV_{\rm rms}$ (MIS = 0)			70	110		kΩ	6
on MICX	$V_{\text{MICX}} = 5 \text{ mV}_{\text{rms}}$				35	55		kΩ	-
CMRR common mode	$G_T = at maximum$					65		dB	6
rejection ratio	•	<u> </u>							
Voltage step on pin 26	I _L =28 mA and 60								
when going from transmis-	$V_{\rm MIC} = 0 (\rm MIS = 0)$				-75		+75	mV	6
sion to mute mode	$V_{\text{MICX}} = 0 \text{ (MIS} =$: 1)							
Bit IM from 0 to 1	At maximum gain								
Dynamic limiter (anti-clippir			6.8 MΩ	operat	ional only	on MIC1	/MIC2	-	
Output voltage swing	TX2 TX1 TX	0							
(peak to peak value)		10 15			3.3		4.4	V _{pp}	6
	$V_{\text{MIC}} = 4 \text{ mV}_{\text{rms}} +$								
Delta output voltage swing	TX2 TX1 TX	.0			200		200		
	$\begin{vmatrix} 0 & 0 & 0 \\ V_{\rm V} = 0 \text{ mV} \end{vmatrix}$	10 dP			-200	0	200	mV _{pp}	6
	$V_{\rm MIC} = 9 {\rm mV_{rms}} +$	10 UD							

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Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Delta output voltage swing	$\begin{array}{l} TX2 TX1 TX0 \\ 0 0 0 & IL = 60 \ mA \\ AT1 = AT0 = 1 \\ V_{MIC} = 22 \ mV_{rms} + 10 \ dB \end{array}$	-200	0	200	mV _{pp}	6
Line distortion (on 600 Ω)	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			2 3 2 3.5 3 3	% % % %	6
Squelch function CA	$AL = 470 \text{ nF}, \text{RAL} = 68 \text{ k}\Omega$			1	1	
Dynamic range attenuation	(note 2) $I_L = 28 \text{ mA and } 60 \text{ mA}$	8.3	9.3	10.3	dB	6
Squelch inhibition (tested on GT)	$\begin{split} \Delta G_T &= G_{T1}(ISQ = 1) - G_{T2}(ISQ = 0) \\ G_{T1} & (V_{MIC} = 160 \ \mu V_{rms}), \\ G_{T2} & (V_{MIC} = 3 \ m V_{rms}) \\ At maximum gain \end{split}$	-0.3	0	0.3	dB	6

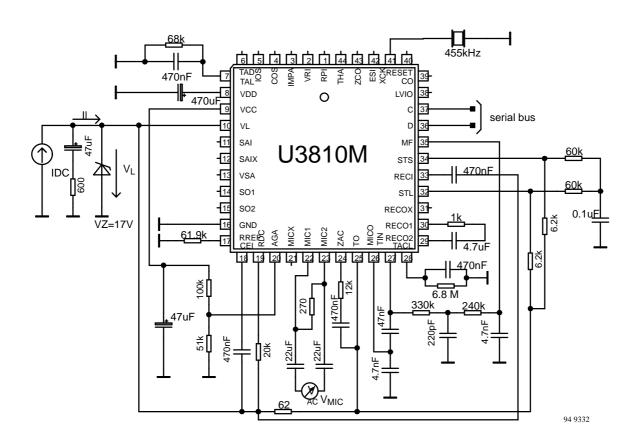


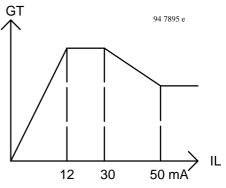
Figure 6 Test circuit

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- Note 1: transmit gain: $G_T = V_L/V_{MIC}$ on MIC1/MIC2 $G_T = V_L/V_{MIC}$ on MICX with the above values of RAG1 and RAG2
- Note 2: Squelch dynamic range: $\Delta G_T = G_{T0} G_{T1}$ G_{T0} measured at $V_{MIC} = 1 \text{ mV}_{rms}$ G_{T1} measured at $V_{MIC} = 160 \mu V_{rms}$



Parameters	Test condition	ons		Min.	Тур.	Max.	Unit	Fig.
Receive	•							
G_R receiving gain $G_R = V_R^*/V_L$ (for normal output)	$V_{GEN} = 0.3 V_{rms}$ $RX2$ maximum gain 1 minimum gain 0	RX1 1 0	RX0 1 0	3.5 -3.7	4.5 -2.5	5.5 -1.3	dB dB	7
$\Delta G_{\rm R} = V_{\rm R}/V_{\rm RECOX}$	$V_{\text{GEN}} = 0.3 \text{ V}_{\text{rms}}$			14.0	15.0	16.0	dB	7
Gain adjustment at earphone	$I_L = 28$ mA and 60 mA Attenuation between two s (both on REC01/REC02 a RECOX)			0.8	1.0	1.3	dB	7
Receiving gain without AGC $G_R = V_R/V_L$	$V_{GEN} = 0.3 V_{rms}$ I IBAL = 1 Bits RX2	Bit: AGC	=1 RX0					
$G_{R} \text{ at } 28 \text{ mA}$ $\Delta G_{R} \text{ at } 20 \text{ mA} < I_{L} < 28 \text{ mA}$ $\Delta G_{R} \text{ at } 28 \text{ mA} < I_{L} < 60 \text{ mA}$	1 1 1	1 1 1	1 1 1	$-3 \\ -0.5 \\ -0.5$	$-1.5 \\ 0 \\ 0$	0 0.5 0.5	dB dB dB	7
ΔG_R receiving gain betw. 28 and 60 mA on RECO1/RECO2 and on RECOX	$V_{GEN} = 0.3 V_{rms}$ Bits	AR1 0 0 1 1	AR0 0 1 0 1	3.6 4.9 6.3 7.5	4.1 5.5 6.9 8.3	4.6 5.9 7.4 8.7	dB dB dB dB	7
+6 dB delta receiving gain on RECO1/RECO2 and on RECOX	$V_{GEN} = 0.3 V_{rms}, I_L = 28n$ (At maximum and minimu			5.6	6.1	6.7	dB	7
Muted gain	$V_{GEN} = 0.3 V_{rms}$ Mute on REC01/REC02 B RECOX Bit	Bit it IE1 = I IR=1	IR=1 E2 = 1	65 60 36			dB dB dB	7
Noise at earpiece psophometric weighted	At maximum gain V _{GEN} = 0 V				150	220	μVp	7
Receiving distortion	$I_L = 28 \text{ mA and } 60 \text{ mA}$ max gain, RX6 = 1 VR = min. gain, RX6 = 0 VR =				1	3	%	7
Receiver output impedance on RECO1/RECO2 (pins 29–30)	$V_R = 50 \text{ mV}_{rms}$,			40	65	85	Ω	7
Receiver output impedance on RECOX (pin 31) * VR = VRECO1 – VRECO2	$V_{RECOX} = 50 \text{ mV}_{rms}$			800	950	1100	Ω	7

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Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Receiver output offset (pin 29 – 30)	$I_L = 28 \text{ mA and } 60 \text{ mA}$ Maximum gain RX6 = 1	-800		+600	mV	7
Automatic sidetone balancing (V _R */V _{MIC})			24 16		dB dB	6
Digital balanced sidetone tested on receiving gain V_R/V_L	$ \begin{array}{c c} V_{GEN} = 0.3 \ V_{rms} & maximum gain \\ close \ switch \ S1 & Bit \ IBAL = 1 \\ & Bits \ BAL2 & BAL1BAL0 \\ & 0 & 0 & 0 \\ & 0 & 0 & 1 \\ & 0 & 1 & 0 \\ & 0 & 1 & 1 \\ & 1 & 0 & 1 \\ & 1 & 1 & 0 \\ & 1 & 1 & 1 \end{array} $	18.0 16.9 15.5 4.2	19.0 17.9 16.5 14.5 12.3 9.2 5.7	20.0 18.9 17.5 7.2	dB dB dB dB dB dB dB dB	7
Confidence level attenuation	$V_{\text{MIC}} = 2 \text{ mV}_{\text{rms}}$ Bit $I_{\text{R}} = 1$	60			dB	6
Confidence level gain V_R/V_{MIC}	$V_{\text{MIC}} = 2 \text{ mV}_{\text{rms}}$ $I_{\text{R}} = 1$ $\text{EC} = 1$	19.5	22.0	23.5	dB	6
Z line match. impedance	$V_{GEN} = 0.3 V_{rms} I_L = 28 \text{ and } 60 \text{ mA}$	520	570	620	Ω	7

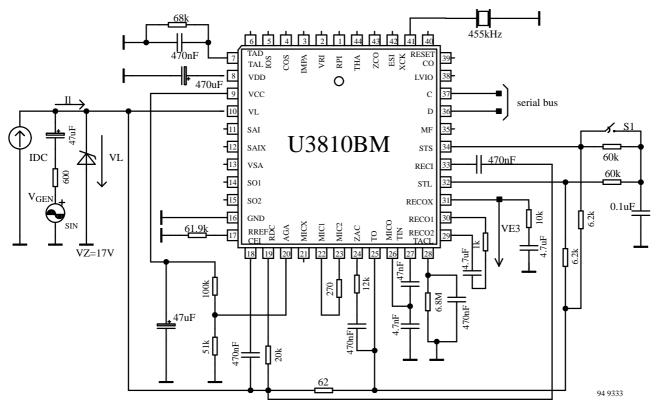


Figure 7 Test circuit

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Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Speaker amplifier						
VSA shunt regulator power supply (pin 13) in transmission mode	Speaker amplifier without signal EA = 1 IL = 28 mA IL = 60 mA	4.0 7.85	4.3 8.3	4.6 8.7	V V	8
Loudhearing gain (note3) from SAI/SAIX to SO1, SO2	$\begin{array}{ll} \text{GSA1} = \frac{\text{VSO1} - \text{VSO2}}{\text{VSAI}} & \text{EA} = 1 \\ \text{GSA2} = \frac{\text{VSO1} - \text{VSO2}}{\text{VSAIX}} \\ \text{Bits} \\ \text{NEA2} & \text{NEA1} & \text{NEA0} & \text{VSAI} = \text{VSAIX} \\ 1 & 1 & 1 & \text{VSAI} = 3.5 \text{mV}_{\text{rms}} \\ 0 & 0 & 0 & \text{VSAI} = 88 \text{mV}_{\text{rms}} \end{array}$	33 5	34	35	dB dB	8
Loudhearing gain between 28 and 60 mA GSA1 and GSA2 (note 3)	EA = 1	-0.5	0	0.5	dB	8
Gain adjustment of speaker amplifier	EA = 1 gain change between two steps	3.8	4.0	4.2	dB	8
Distortion (measured on 100 Ω load)	$ \begin{array}{c} EA = 1 \\ Bits \\ NEA2 \ NEA1 \ NEA0 \ VSAI \\ 1 \ 1 \ 1 \ VSAI = 12 \ mV_{rms} \\ VSAI = 30 \ mV_{rms} \\ 0 \ 0 \ VSAI = 250 \ mV_{rms} \\ \end{array} \\ \begin{array}{c} Bits \ EA = 1 \\ NEA2 \ NEA1 \ NEA0 \\ 1 \ 1 \ 1 \ VSAI = 80 \ mV_{rms} \\ \end{array} $			2.0 4.0 1.5 2.0	% % %	8
Input impedance SAI SAIX	$\begin{array}{c cccc} 0 & 0 & 0 & VSAI = 250 \text{ mV}_{rms} \\ \hline EA = 1 \end{array}$	4	7 7	2.0 10 10	% kΩ	8
Confidence gain in loud- hearing	$V_{MIC} = 4 \text{ mV} \qquad \frac{VSO}{V_{MIC}} EA = 1$ $V_{MIC} EC = 1, \text{ ITAL} = 1$	36	7	40	dB	8
Loudhearing input cross talk attenuation		60 60			dB dB	8
Output power (Note 4, 6)	$ \begin{array}{c} & 50 \ \Omega \ \text{load} asym. \\ \text{EA = 1} & I_L = 20 \ \text{mA} & 100 \ \Omega \ \text{load} sym. \\ I_L = 28 \ \text{mA} & 50 \ \Omega \ \text{load} asym. \\ 100 \ \Omega \ \text{load} sym. \\ 100 \ \Omega \ \text{load} sym. \\ I_L = 60 \ \text{mA} & 50 \ \Omega \ \text{load} asym. \\ 100 \ \Omega \ \text{load} sym. \\ 100 \ \Omega \ \text{load} sym. \\ 100 \ \Omega \ \text{load} sym. \end{array} $	9.0 19.0 140	12,5 11,5 24 30 120 170		mW mW mW mW	8
Output offset (pin 14 – 15)	$LIS = 0, 1 \qquad EA = 1$ max. and min. gain	-200		+200	mV	8
Leakage current (pin 6)	EA = 1			140	nA	8
Offset (pin 7)	$ \begin{array}{ll} RAL = 68 \ k\Omega & I_L = 28 \ mA \ and \ 60 \ mA \\ EA = 1 \end{array} $			140	mV	6
Antilarsen system	$CAL = 470 \text{ nF}, \text{RAL} = 68 \text{ k}\Omega$					
Dynamic range attenuation	(note 5) IL = 28 mA and 60 mA EA = 1 VSAI = 6 mV _{rms} Bit ISQ = 0 BIT ISQ = 1	11 23	12 26	13 29	dB dB	8

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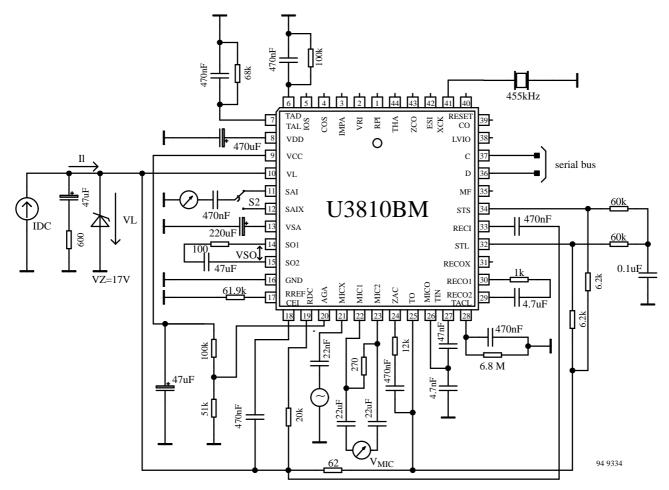


Figure 8 Test circuit

- Note 3: GSA1 measured with S2 on 11 GSA2 measured with S2 on 12 and Bit LIS = 1
- Note 4: Antilarsen dynamic range: $\Delta GLS = GLSA - GLSB$ GLSA measured at $V_{MIC} = 160 \ \mu V_{rms}$ GLSB measured at $V_{MIC} = 1 \ m V_{rms}$
- Note 5: The available output current of the speaker amplifier can be increased by reduction of the quiescent current of the receiver output stage (bits IE1, IE2, see "contents of internal registers").

DTMF dialing

The output pin MF provides the multifrequency signal to be transmitted on line. This signal is the result of the sum of two frequency pulse modulations and requires an external filter to compose a dual sine wave. The frequencies are chosen in a low group and a high group. The circuit conforms to the T/CS 46–02 CEPT recommendation concerning DTMF option 1 (-9/-11 dBm) and option 2 (-6/-8 dBm) transmit level 5 (example: in fig. 6, option 2 can be fulfilled with 3.5 dB pre–emphasis and 1.5 Vpp low frequency level pin 35).

Two different low levels (with 3 dB difference) and two different pre–emphasis (2.5 and 3.5 dB) can be chosen through the serial bus.

Melody – confidence tone

Melody/confidence tone frequencies are given in table 2.

In the state SIN1 = 1, SIN0 = 0, the IC delivers a single pulse density modulated frequency at pin MF (the same behavior as DTMF), denoted as a confidence tone. The confidence tone is sent either to the line or on the earpiece. In the state SIN1 = 0, SIN0 = 1, a square wave is sent to the loudhearing input for ringing melodies.

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Table 1: Frequency tolerance of the output tones for DTMF signalling tone output frequency when using 455 kHz

Standard frequency	Tone output				
Hz	frequency Hz	%	Hz		
Low Group					
697	697.85	0.12	+0.85		
770	771.18	0.15	+1.18		
852	852.06	0.01	+0.06		
941	940.08	-0.10	-0.92		
High Group					
1209	1210.1	0.09	+1.1		
1336	1338.2	0.17	+2.2		
1477	1477.3	0.02	+0.3		
1633	1636.7	0.22	+3.7		

Note: Frequency can be directly measured on CO when S3 is closed (figure 9)

AMF	SIN0	SIN1	СО
1	1	1	DTMF : HF
0	1	1	DTMF : LF
0	1	0	MELODY
0	0	1	CONFIDENCE TONE

	1209	1336	1477	1633
697	1	2	3	А
770	4	5	6	В
852	7	8	9	С
941	*	0	#	D

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Standard	Tone output	Frequency
frequency	frequency	deviation
Hz	Hz	⁰ / ₀₀
440	440.04	0.09
466.16	466.19	0.06
493.88	493.49	-0.78
523.25	522.99	-0.50
554.36	554.88	0.92
587.33	587.86	0.89
622.25	621.58	-1.07
659.25	659.42	0.26
698.46	697.85	-0.87
740	741.04	1.41
784	784.48	0.62
830	830.29	-0.37
880	878.38	-1.84
932.3	932.38	0.08
987.77	989.13	1.38
1046.5	1048.39	1.80
1108.73	1109.76	0.93
1174.66	1172.68	-1.69
1244.5	1243.17	-1.07
1318.5	1315.03	-2.63
1396.9	1395.71	-0.86
1480	1477.27	-1.84
1568	1568.97	0.62
1661.2	1660.58	-0.37
1760	1763.57	2.03
1864.65	1864.75	0.06
1975.5	1978.26	1.40
2093	2087.16	-2.79
2217.46	2208.74	-3.93
2349.3	2345.36	-1.68

Table 2:Frequency tolerance of the output toneTone output frequency when using 455 kHz

Parameters		Test conditions		Тур.	Max.	Unit	Fig.
DTMF generation (specified	pin MF)						
Tone frequency accuracy	See table 1						
Low group tone level without attenuation	Note 7 S3 closed	BFOA (pre-emphasis A) BFOB (pre-emphasis B)	1.35 1.25	1.50 1.40	1.65 1.55	V V	9
High group tone level without attenuation	Note 7 S3 closed	HFOA (pre-emphasis A) HFOB (pre-emphasis B)	1.80 1.90	2.00 2.10	2.20 2.35	V V	9
Pre-emphasis A without attenuation	Note 7 S3 closed	PROA	2.04	2.54	3.04	dB	9
Pre-emphasis B without attenuation	Note 7 S3 closed	PROB	3.02	3.52	4.02	dB	9
Low group tone level with attenuation	Note 7 S3 closed	BF1A (pre-emphasis A) BF1B (pre-emphasis B)	0.95 0.90	1.05 1.00	1.15 1.10	V V	9
High group tone level with attenuation	Note 7 S3 closed	HF1A (pre-emphasis A) HF1B (pre-emphasis B)	1.25 1.35	1.40 1.50	1.55 1.65	V V	9



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Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Pre-emphasis A with attenuation	Note 7 PR1A S3 closed	2.04	2.54	3.04	dB	9
Pre-emphasis B with attenuation	Note 7 PR1B S3 closed	3.02	3.52	4.02	dB	9
Leakage	$\begin{array}{c cccc} S4 = 2 & Bits & SIN1 & SII \\ S3 closed & 0 & 0 \end{array}$			100	nA	9
Distortion at line	$IL = 28 \text{ mA} M = 8 \text{ Key} = (3)^{\circ}TX6 = 1 IM = 1$		1	3	%	6
Low group tone level at line	IL = 28 mA and 60 mA M = 8 Key = «3» TX6 = 1 IM = 1	-10	-8	-6	dBm	6
Melody generation						
Tone frequency accuracy	see table 2					
Confidence tone level	Note: 7 CTL	2.10	2.33	2.60	V	9

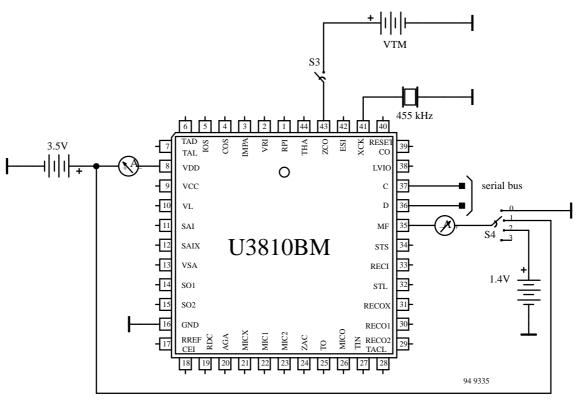


Figure 9 Test circuit

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		Internal set by set			Internal signal set by clock count			
S4 (Fig. 9)	AMF	SIN1	SIN0	M4	FB	FH	F227	I measured
0	0	1	1	0	1	0	X	I1
0	0	1	1	0	0	1	X	I2
0	0	1	1	1	0	1	Х	I3
0	0	1	0	0	0	Х	1	I4
0	1	1	1	Х	0	0	1	15
1	0	1	1	1	0	1	Х	I6
1	0	1	1	0	1	0	Х	Ι7
1	0	1	1	1	1	0	Х	18
1	0	1	0	Х	1	X	0	I9
1	1	1	1	Х	1	1	0	I10

X: either 1 or 0

Note 7: DTMF calculations

BF level without attenuation with pre-emphasis A:	$BFOA = \left(\frac{I1}{I1 + I7} + \frac{I6}{I6 + I2}\right)\frac{VDD}{2}$
BF level without attenuation with pre-emphasis B:	BFOB = $\left(\frac{I1}{I1 + I8} + \frac{I6}{I6 + I3}\right)\frac{VDD}{2}$
HF level without attenuation with pre-emphasis A:	$\text{HFOA} = \left(\frac{\text{I2}}{\text{I2} + \text{I6}} + \frac{\text{I7}}{\text{I7} + \text{I1}}\right)\frac{\text{VDD}}{2}$
HF level without attenuation with pre-emphasis B:	HFOB = $\left(\frac{I3}{I3 + I6} + \frac{I8}{I8 + I1}\right)\frac{VDD}{2}$
Pre-emphasis A without attenuation:	$PROA = 20 \log \left(\frac{HFOA}{BFOA}\right)$
Pre-emphasis B without attenuation:	$PROB = 20 \log \left(\frac{HFOB}{BFOB}\right)$
BF level with attenuation with pre-emphasis A:	$BF1A = \left(\frac{I1}{I1 + I7 + I10} + \frac{I6}{I6 + I2 + I5}\right)\frac{VDD}{2}$
BF level with attenuation with pre-emphasis B:	$BF1B = \left(\frac{I1}{I1 + I8 + I10} + \frac{I6}{I6 + I3 + I5}\right)\frac{VDD}{2}$
HF level with attenuation with pre-emphasis A:	$HF1A = \left(\frac{I2}{I2 + I6 + I10} + \frac{I7}{I7 + I1 + I5}\right)\frac{VDD}{2}$
HF level with attenuation with pre-emphasis B:	$HF1B = \left(\frac{I3}{I3 + I6 + I10} + \frac{I8}{I8 + I1 + I5}\right)\frac{VDD}{2}$
Pre-emphasis A without attenuation:	$PR1A = 20 \log \left(\frac{HF1A}{BF1A}\right)$
Pre-emphasis B without attenuation:	$PR1B = 20 \log \left(\frac{HF1B}{BF1B}\right)$
Confidence tone level:	$CTL = \left(\frac{I1}{I1 + I9} + \frac{I6}{I6 + I4}\right)\frac{VDD}{2}$

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Parameters	Test conditions	Min.	Тур.	Max.	Unit	Fig.
Ringer						
THA threshold voltage THTV	$V_S = 5 V$ S5 on 1	8.30	8.75	9.20	V	10
THA hysteresis ∆TH	$V_S = 5 V$ S5 on 1	435	465	495	mV	10
VSA threshold voltage VSAON (ring detector en- abled)	VTHA = 12 V S5 on 1	3.0	3.2	3.4	V	10
VSA threshold voltage VSAOFF (ring detector dis- abled)	VTHA = 12 V S5 on 1	2.45	2.5	2.65	V	10
Switching supply output current		33	37		mA	10
Input impedance VIN/IIN		50.0 2.78 13.4	2.90 14.1	3.05 15.0	kΩ kΩ kΩ	10
RPI ringing power information		1.48 1.57	1.55 1.61	1.64 1.64	V V	10
VSA/VDD switch off VSA- OFF1 (measured on VSA)	S8 closed S5 on 1 IVDD = -1 mA	5.55	5.8	6.0	V	10
VSA shunt regulator VSAL VSAH	S5 on 3 $ISA = 2 mA$ ISA = 45 mA	4.75 5.0	5.0 5.3	5.15 5.7	V V	10
Difference between max. VSA voltage and cut off voltage	VSADIFF = VSAOFF1 – VSAH	250	500		mV	10
ZCO Zero crossing information		4.4		0.5	V V	10
Ringer output power (on 100 Ω load)	$ \begin{array}{lll} VIN = 30 \ V & RIN = 300 \ k\Omega \\ S7 \ on \ 2 & S5 \ on \ 2 \\ SIN1 \ SIN0 & LIS & EA \\ 0 & 1 & 1 & 1 \\ NEA - maximum \ gain \end{array} $	70	105	130	mW	10
Extra ringing attenuation	$VIN = 30 V RIN = 300 k\Omega$ S7 on 2 S5 on 2 SIN1 SIN0 LIS AMF EA 0 1 1 1 1 NEA – maximum gain	-12.8	-12.2	-11.6	dB	10

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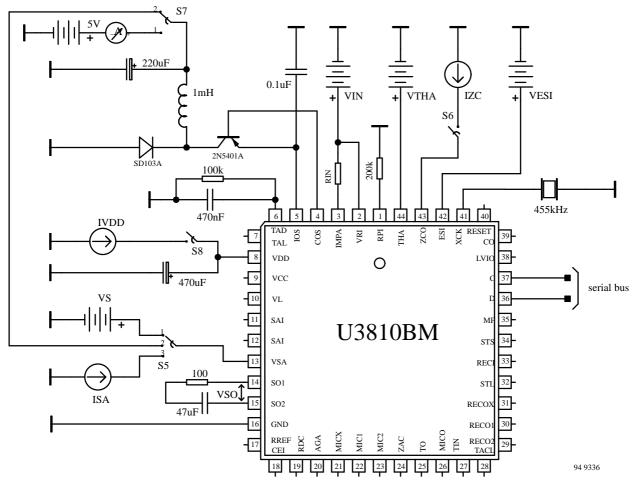
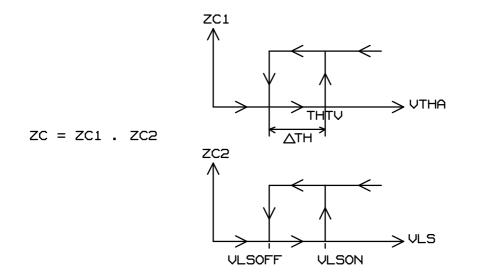


Figure 10 Test circuit



937608

Electrical characteristics of logical part

$f_{xck} = 4$	455	kHz
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VDD = 3.5 V

Parameter	Min.	Тур.	Max.	Unit
INPUTS : C, D Low-voltage input Vil High-voltage input Vih	2.8		0.7	V V
Input leakage current Ii (0 < VI < VDD)	-1		1	μΑ
Output: RESET, CO, LVIO Low-voltage output (Iol = 100 μ A) Vol High-voltage output (Ioh = -100 μ A) Voh	3.1		0.35	V V
CLOCK: CO (fig. 15)Using reference ceramic resonatorperiod: t_{cyc} High pulse width: t_{wch}	2.19 1.10	2.20	2.21 1.45	μs μs
$\begin{array}{c c} \text{SERIAL BUS (figure 19)} \\ \text{Data set-up time} & t_{\text{sud}} \\ \text{Data hold time} & t_{\text{hd}} \\ \text{Clock low time} & t_{\text{cl}} \\ \text{Clock high time} & t_{\text{ch}} \\ \text{Hold time before transfer condition} & t_{\text{eon}} \\ \text{Data low pulse on transfer condition} & t_{\text{eh}} \\ \text{Data high pulse on transfer condition} & t_{\text{eoff}} \\ \end{array}$	0.1 0 2 2 0.1 0.2 0.2			μs μs μs μs μs μs μs
RESET TIMING (figure 11, 12 and 13)Clock start-up time t_{on} Clock inhibition time t_{off} Reset time (without t_{on}) t_r	70 30	3 31.6	5 150 32	ms μs ms

Power-on-reset and reset pin

The system (U3810BM + microcontroller) is woken up by an initial condition:

- line voltage (VL)
- ringer (THA)
- external supply (ESI)

1.) Power on in speed-up condition (VDD < VSON)

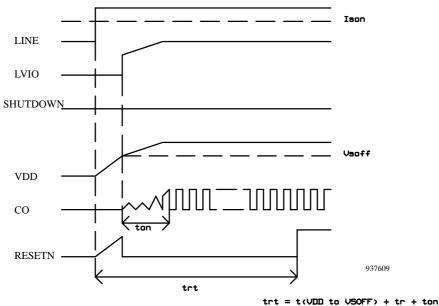
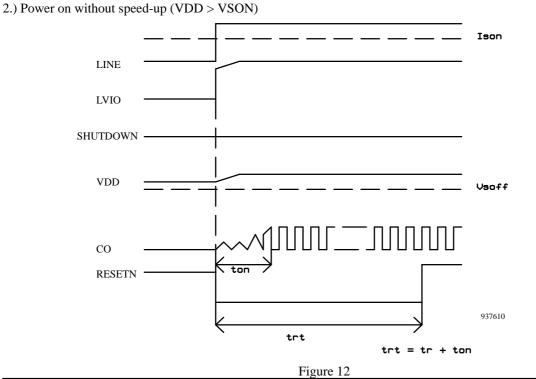


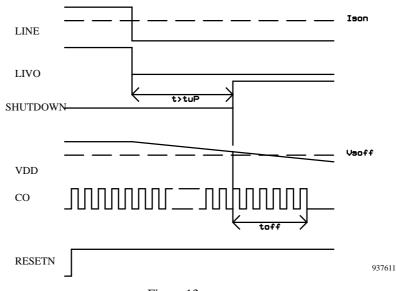
Figure 11



To avoid undefined states of the system when it is powered on, an internal reset clears the internal registers, and maintains pin RESET low during trt.

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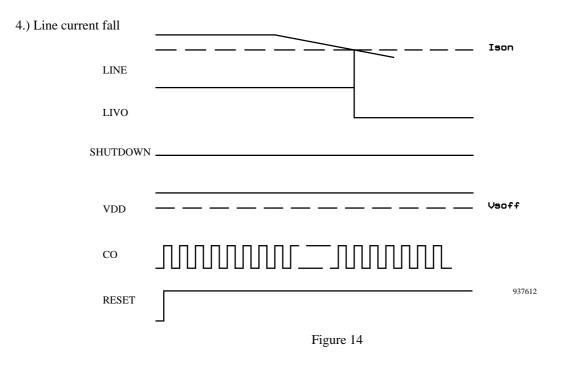
3.) Line break





When the microprocessor detects LIVO low during $t > t\mu P$ (internal microprocessor timing special for line breaks), it forces high the shutdown bit through the serial bus, thus leading the IC, after t_{off} , to go into standby mode (oscillator stop). Pin RESET remains high.

When the line break is shorter than $t\mu P$, nothing appears.



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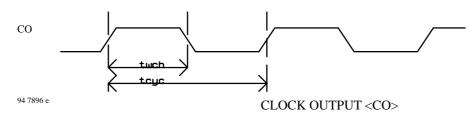


Figure 15

Serisl bus

The circuit is remoted by an external microcontroller through the serial bus:

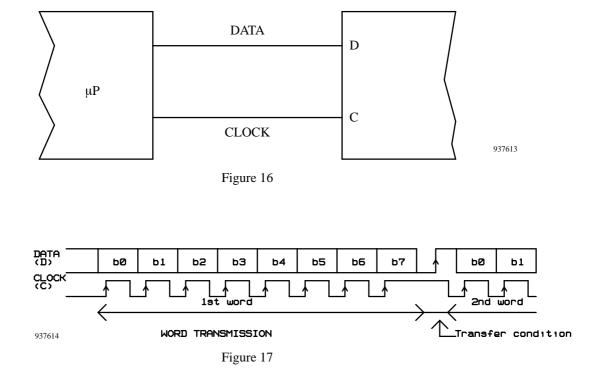
The data is an 8-bit word:

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- B7 B6 B5: address of the destination register (0 to 7)
- B4 B0: contents of register

The data line must be stable when the clock is high and data must be serially shifted.

After 8 clock periods, the transfer to the destination register is (internally) generated by a low to high transition of the data line when the clock is high.



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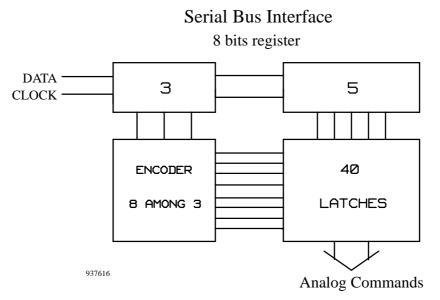
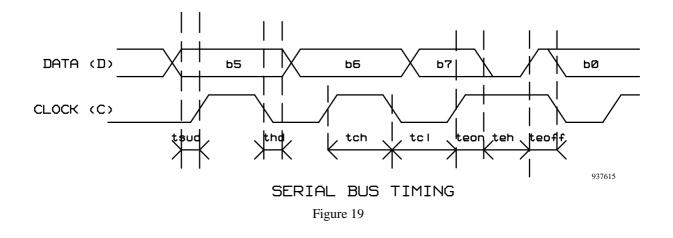


Figure 18



Content of internal registers

0: Transmission mode

MIS	TX6	TX2	TX1	TX0	MIS: TX6: TX:	Microphone input switching +6dB Transmission gain adjustment
1: Reception r	node					
LIS	RX6	RX2	RX1	RX0	LIS: RX6: RX:	Loudhearing input switching +6dB Reception gain adjustment

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2: Loudhearing mode

IAL	EA	NEA2	NEA1	NEA0	IAL: EA: NEA:	Antilarsen inhibition Loudhearing enable Loudhearing gain adjustment
3: AGC mode						
IAGC	AR1	AR0	AT1	AT0	IAGC: AT: AR:	AGC inhibition Transmission AGC adjustment Reception AGC adjustment
4: Sidetone m	ode					
					IE3.	Pacantian output amplifiar current

IE2	IBAL	BAL2	BAL1	BAL0	IE2: IBAL:	Reception output amplifier current adjustment Inhibition of automatic sidetone balance
-----	------	------	------	------	---------------	---

BAL	Z
0	1 STS
1	5/6 STS + 1/6 STL
2	2/3 STS + 1/3 STL
3	1/2 STS + $1/2$ STL
4	1/2 STS + 1/2 STL
5	1/3 STS + 2/3 STL
6	1/6 STS + 5/6 STL
7	1 STL

5: Internal inhibitions

IR	EC	IT	IM	IE1	IR: EC: IT: IM: IE1:	Reception inhibition Confidence enable Transmit inhibition Microphone inhibition Reception output amplifier current adjustment
----	----	----	----	-----	----------------------------------	---

IE1	IE2	IREC	
0	0	3 mA	
0	1	2 mA	
1	0	1 mA	
1	1	0 mA	Earpiece inhibition

6: Melody / DTMF choice

M4	M3	M2	M1	M0	
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U3810BM

X		1	DTMF	mode
М	Melody or confidence tone out- put		Key	HF/LF
00	A3	440.0	«1»	2.5 dB
01	A#3	466.2	«4»	"
02	B3	493.5	«7»	"
03	C4	523.0	«*»	"
04	C#4	554.9	«2»	"
05	D4	587.8	«5»	"
06	D#4	621.6	«8»	"
07	E4	659.4	«0»	,,
08	F4	697.8	«3»	,,
09	F#4	741.0	«б»	,,
0A	G4	784.5	«9»	"
OB	G#4	830.3	«#»	"
OC	A4	878.4	«A»	"
0D	A#4	932.4	«B»	"
0E	B4	989.1	«C»	"
0F	C5	1048.4	«D»	"
10	C#	1109.7	«1»	3.5 dB
11	D5	1172.7	«4»	"
12	D#5	1243.2	«7»	"
13	E5	1315.0	«*»	"
14	F5	1395.7	«2»	"
15	F#5	1477.3	«5»	"
16	G5	1569.0	«8»	"
17	G#5	1660.6	«0»	"
18	A5	1763.6	«3»	"
19	A#5	1864.7	«б»	,,
1A	B5	1978.3	«9»	,,
1B	C6	2087.2	«#»	,,
1D 1C	C#6	2208.7	«A»	,,
1D	D6	2345.4	«B»	,,
1E	20	201011	«C»	,,
112 11F			«C» «D»	,,
11			ND "	

Table 3

7: Control register

AMF	ISQ	SD	SIN1	SINO	AMF: ISQ: SD: SIN:	MF output attenuation -3 dB extra ringing attenuation (12 dB) Squelch inhibition Shutdown Generator mode 0: OFF 1: Melody (Ringer) 2: Confidence tone 3: DTMF
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Order Information

Package	Туре
PLCC 44	U3810BM-CP
SSO 44	U3810BM-FN

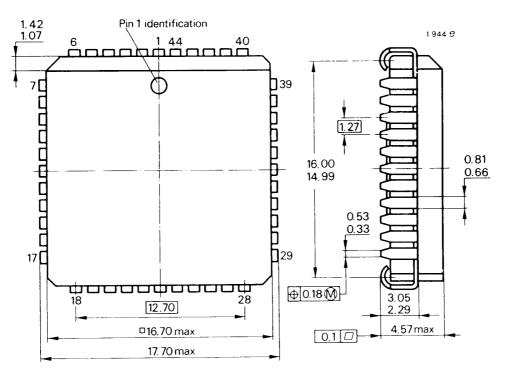
Electrostatic sensitive device. Observe precautions for handling.



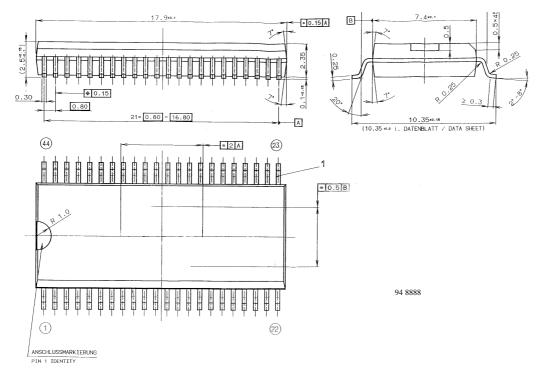
TELEFUNKEN Semiconductors

Dimensions in mm

Package: PLCC 44



Package: SSO 44



OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements and
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

Of particular concern is the control or elimination of releases into the atmosphere of these substances which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) will severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of any ODSs listed in the following documents that all refer to the same substances:

- (1) Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- (2) Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA and
- (3) Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with and do not contain ozone depleting substances.

We reserve the right to make changes to improve technical design without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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